

IN THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

- [1] (Original) A light-emitting diode having a light-emitting element fixed to a leadframe with a conductive adhesive material, the light-emitting element having a semiconductor layer including a light-emitting layer laid on a first surface of a translucent substrate, of which a second surface facing away from the first surface is used as a light emission observation surface,
- wherein a side surface of the semiconductor layer is an inclined surface inclined relative to the first surface, and an angle between a normal to the inclined surface and a crystal surface on which the light-emitting layer grows is equal to an angle at which light emitted by the light-emitting layer is totally reflected toward the translucent substrate.
- [2] (Original) The light-emitting diode of claim 1, wherein the semiconductor layer has a first-conductivity-type semiconductor layer and a second-conductivity-type semiconductor layer formed by laying a first-conductivity-type compound semiconductor and a second-conductivity-type compound semiconductor in this order from a translucent substrate side so that the first-conductivity-type semiconductor layer and the second-conductivity-type semiconductor layer are adjacent to each other with the light-emitting layer sandwiched in between, with a vertical hole formed so deep as to penetrate the translucent substrate and reach the first-conductivity-type semiconductor layer but not to reach the second-conductivity-type semiconductor layer, and with a conductive material formed along the vertical hole so as to conduct to the first-conductivity-type semiconductor layer.
- [3] (Original) The light-emitting diode of claim 1, wherein the semiconductor layer has a first-conductivity-type semiconductor layer and a second-conductivity-type semiconductor layer formed by laying a first-conductivity-type compound semiconductor

and a second-conductivity-type compound semiconductor in this order from a translucent substrate side so that the first-conductivity-type semiconductor layer and the second-conductivity-type semiconductor layer are adjacent to each other with the light-emitting layer sandwiched in between, with an insulating member filling an opening formed in the second-conductivity-type semiconductor layer, with a vertical hole formed above the opening so as to penetrate the translucent substrate and the first-conductivity-type semiconductor layer, and with a conductive material formed along an inner wall surface of the vertical hall so as to conduct to the first-conductivity-type semiconductor layer.

- [4] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 2 [[and 3]], wherein the vertical hole is closed by a pad electrode formed on the second surface of the translucent substrate.
- [5] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 2 [[to 4]], wherein the vertical hole is increasingly small with increasing depth.
- [6] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 2 [[to 5]], wherein the conductive material is translucent.
- [7] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 1 [[to 6]], wherein the angle is in a range from 40° to 50°.
- [8] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 1 [[to 7]], wherein the inclined surface is coated with an insulating film.
- [9] (Currently Amended) The light-emitting diode of ~~one of claims~~ claim 1 [[to 8]], wherein the semiconductor layer is formed of a gallium nitride compound.